

Voids II+

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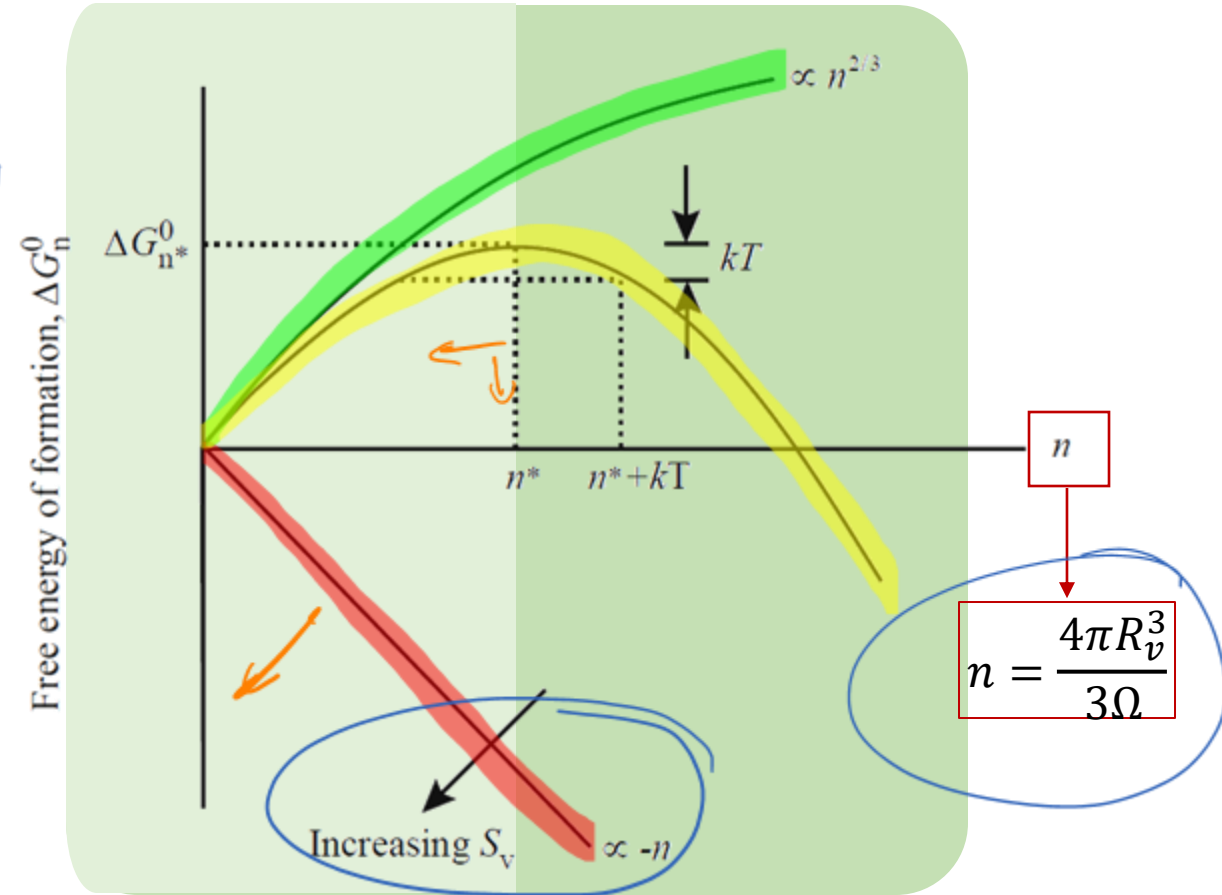
Void Nucleation Theory: Graphical depiction

$$\Delta G_n^0 = \underbrace{-nkT \cdot \ln(S_v)}_{\substack{\text{entropy of} \\ \text{mixing} \\ \text{(negative)}}} + \underbrace{(36\pi\Omega^2)^{1/3}\gamma n^{2/3}}_{\substack{\text{formation of} \\ \text{interfacial} \\ \text{surface} \\ \uparrow 4\pi r^2 \delta}}$$

as decrease

$\uparrow S_v \propto 1/n_{\text{nucl.}}$

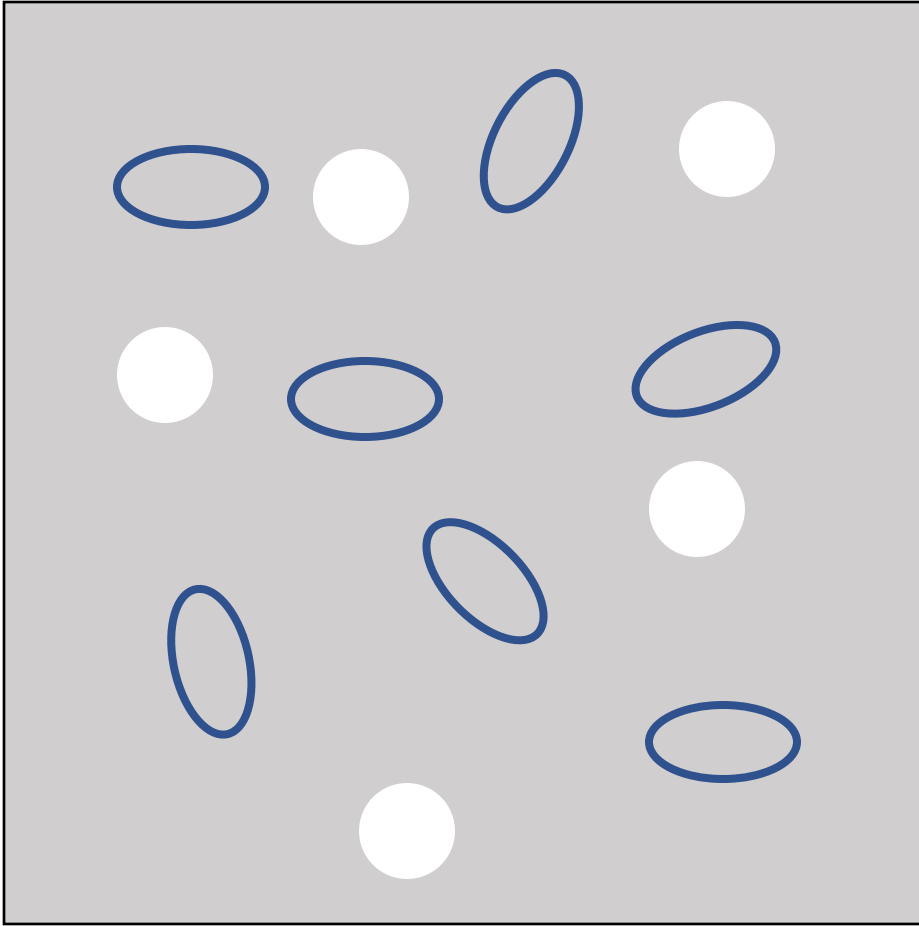
Temp



Full derivations and discussion in Was 8.1

Fig. 8.2 Schematic illustration of ΔG_n^0 , the free energy of formation of a spherical void consisting of n vacancies and the effect of thermal fluctuations on the critical size void embryo

Void Growth – Simple Model



Let's assume a material with nucleated voids and dislocation loops only, then the total sink strength can be defined as (from Table 5.2 Was):

$$k_v^2 = z_v \rho_d + 4\pi R \rho_v$$

$$k_i^2 = z_i \rho_d + 4\pi R \rho_v$$

Void Growth

- For void growth, we need to know the net flux of vacancies to a void embryo. The net rate is thus a combination of the fluxes of interstitials and vacancies to a *nucleated* void, where:

$$J_{net}^V = J_v^V - J_i^V = 4\pi R\Omega D_v(C_v - C_v^V) - 4\pi R\Omega D_i(C_i - C_i^V)$$

$$J_{net}^V = dV/dt = 4\pi R\Omega(D_v C_v - D_i C_i)$$

$$dR/dt = \dot{R} = \frac{\Omega}{R}(D_v C_v - D_i C_i)$$

$$C_v^V = C_v^0 \exp\left(\frac{2\gamma\Omega}{Rk_bT}\right)$$

Void Growth

$$\frac{\partial C_v}{\partial t} = K_0 - K_{iv}C_iC_v - K_{vs}C_vC_s = 0$$

$$C_v = \frac{-K_{is}C_s}{2K_{iv}} + \left[\frac{K_0K_{is}}{K_{iv}K_{vs}} + \frac{K_{is}^2C_s^2}{4K_{iv}} \right]^{1/2}$$

Next slide

$$dR/dt = \dot{R} = \frac{\Omega}{R} (D_vC_v - D_iC_i)$$

$$C_i = \frac{-K_{vs}C_s}{2K_{iv}} + \left[\frac{K_0K_{vs}}{K_{iv}K_{is}} + \frac{K_{vs}^2C_s^2}{4K_{iv}} \right]^{1/2}$$

Next slide

$$\frac{\partial C_i}{\partial t} = K_0 - K_{iv}C_iC_v - K_{vs}C_iC_s = 0$$

Void Growth

Remember:

$$C_v = \frac{-K_{is}C_s}{2K_{iv}} + \left[\frac{K_0K_{is}}{K_{iv}K_{vs}} + \frac{K_{is}^2C_s^2}{4K_{iv}} \right]^{1/2} \quad \text{and} \quad k_{jx}^2 = \frac{K_{jx}C_x}{D_j} \quad \text{and} \quad k_v^2 = z_v\rho_d + 4\pi R\rho_v$$

$$C_i = \frac{-K_{vs}C_s}{2K_{iv}} + \left[\frac{K_0K_{vs}}{K_{iv}K_{is}} + \frac{K_{vs}^2C_s^2}{4K_{iv}} \right]^{1/2} \quad \text{and} \quad k_i^2 = z_i\rho_d + 4\pi R\rho_v$$

You can now pull all three equations above together to get:

$$C_v = \frac{D_v(4\pi R\rho_v + z_v p_d)}{2K_{iv}} (\sqrt{1 + \eta} - 1)$$

$$C_i = \frac{D_i(4\pi R\rho_v + z_i p_d)}{2K_{iv}} (\sqrt{1 + \eta} - 1)$$

Where:

$$\eta = \frac{4K_0K_{iv}}{D_iD_v(4\pi R\rho_v + z_v p_d)^2}$$

Void Growth

- With everything defined,

$$C_v = \frac{D_v(4\pi R\rho_v + z_v p_d)}{2K_{iv}}(\sqrt{1+\eta} - 1)$$

$$C_i = \frac{D_i(4\pi R\rho_v + z_i p_d)}{2K_{iv}}(\sqrt{1+\eta} - 1)$$

$$\eta = \frac{4K_0 K_{iv}}{D_i D_v (4\pi R\rho_v + z_v p_d)^2}$$

$$dR/dt = \dot{R} = \frac{\Omega}{R}(D_v(C_v - C_v^V) - D_i C_i)$$

- We can now rewrite the growth law as:

$$\dot{R}R = \frac{\Omega}{2K_{iv}} D_i D_v (z_i \rho_d - z_v \rho_d) (\sqrt{1+\eta} - 1)$$

Void Growth

$$R\dot{R} = K_o \Omega \left(\frac{z_i - z_v}{z_v} \right) \frac{z_v \rho_d}{(4\pi R \rho_v + z_v \rho_d)(4\pi R \rho_v + z_i \rho_d)} F(\eta)$$

- The **first term** is the main dpa-rate effect on void growth
- The **second term** is the “bias” term: if $z_i = z_v$, void growth is impossible
- The **third term** is the sink-strength balance term. Void growth is eliminated if there are too many or too few dislocations. Optimum growth occurs when the void sink term ($4\pi R \rho_v$) and the dislocation sink term ($z_v \rho_d$) are equal.
- The **fourth term** contains the effect of point defect recombination:

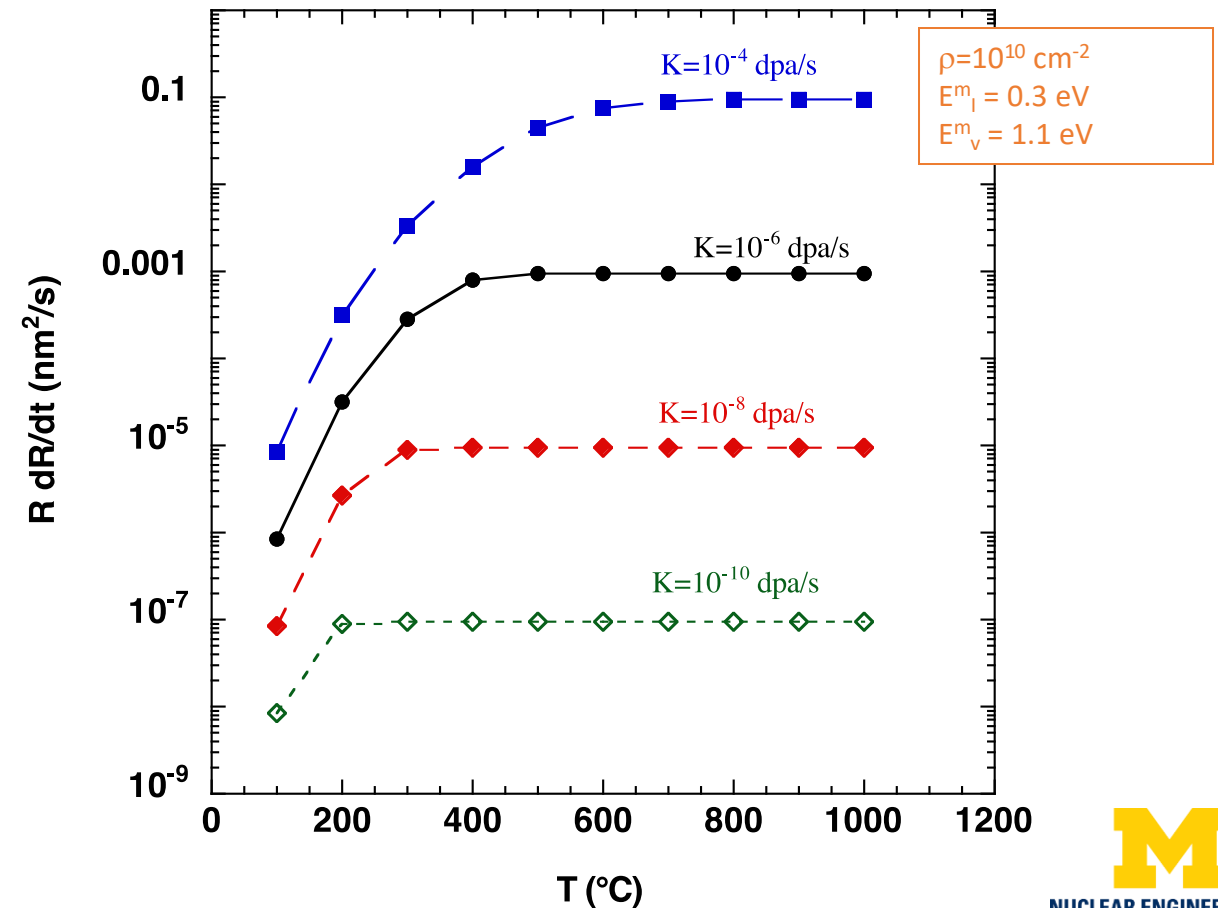
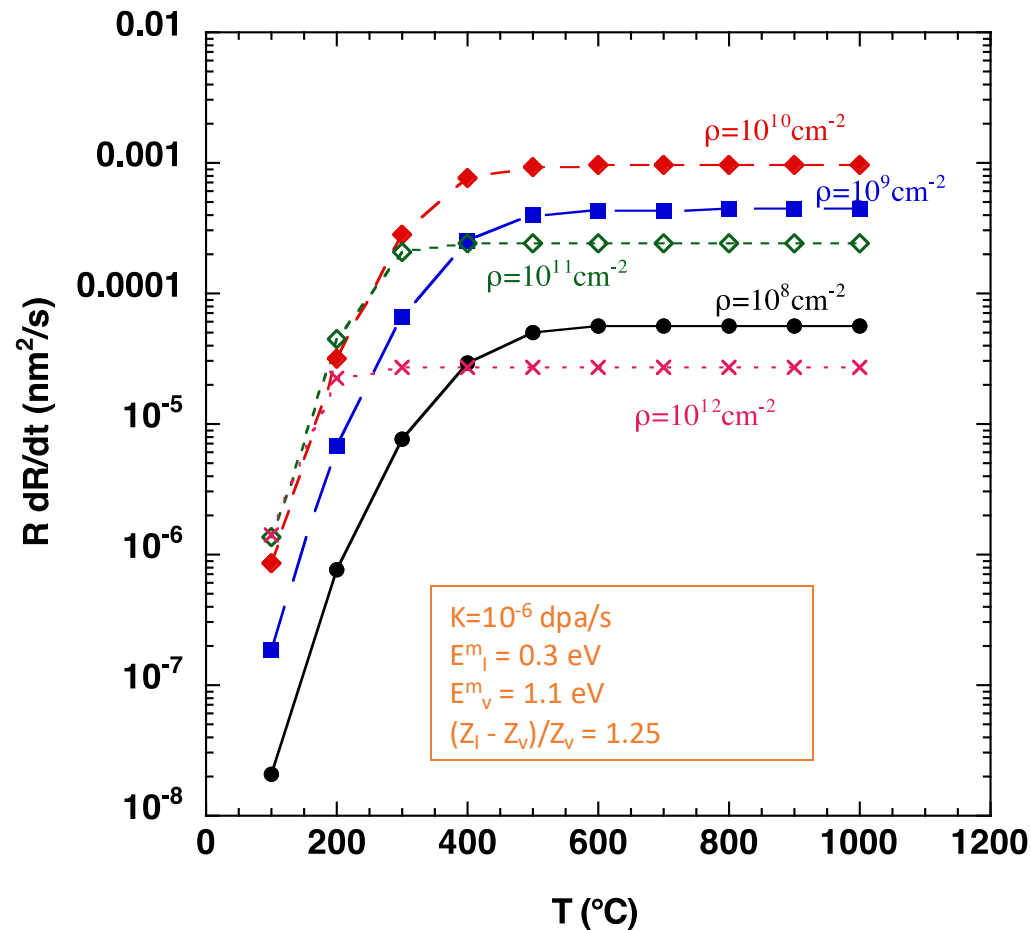
$$F(\eta) = 2(\sqrt{1+\eta} - 1) / \eta$$

Since h decreases with increasing temperature and F decreases with increasing η :

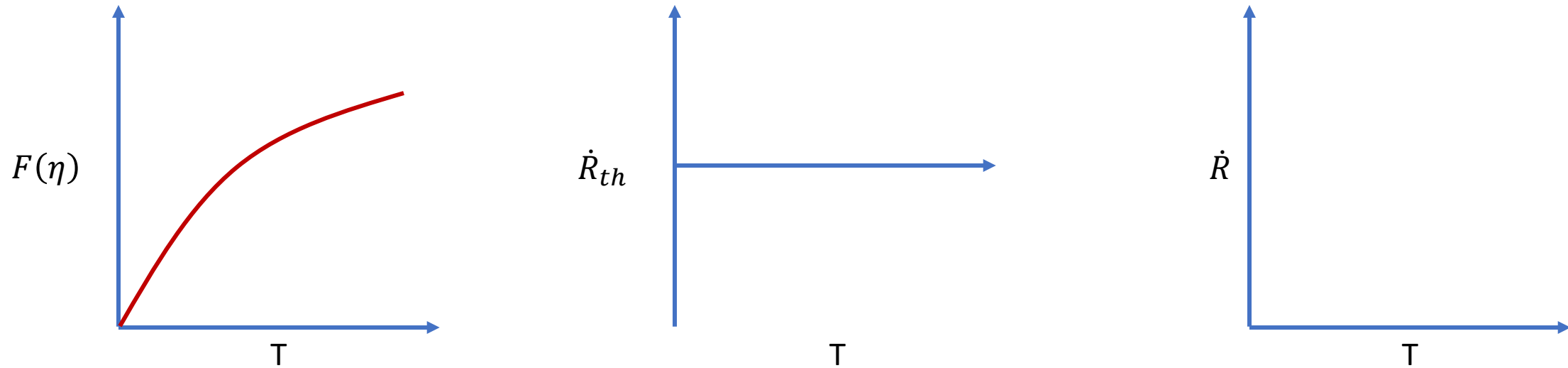
- At high temperature, $F \rightarrow 1$ and recombination does not effect void growth
- At low temperature, $F \rightarrow 0$ and recombination prevents void growth.

Void Growth

$$R\dot{R} = K_o \Omega \left(\frac{z_i - z_v}{z_v} \right) \frac{z_v \rho_d}{(4\pi R \rho_v + z_v \rho_d)(4\pi R \rho_v + z_i \rho_d)} F(\eta)$$



Void Swelling Temperature Dependence



At very high temperatures, void growth ceases because the vacancies “boil off” the voids. Repeating the previous derivation without neglecting C_v^0 gives the following shrinkage rate that competes with the growth rate:

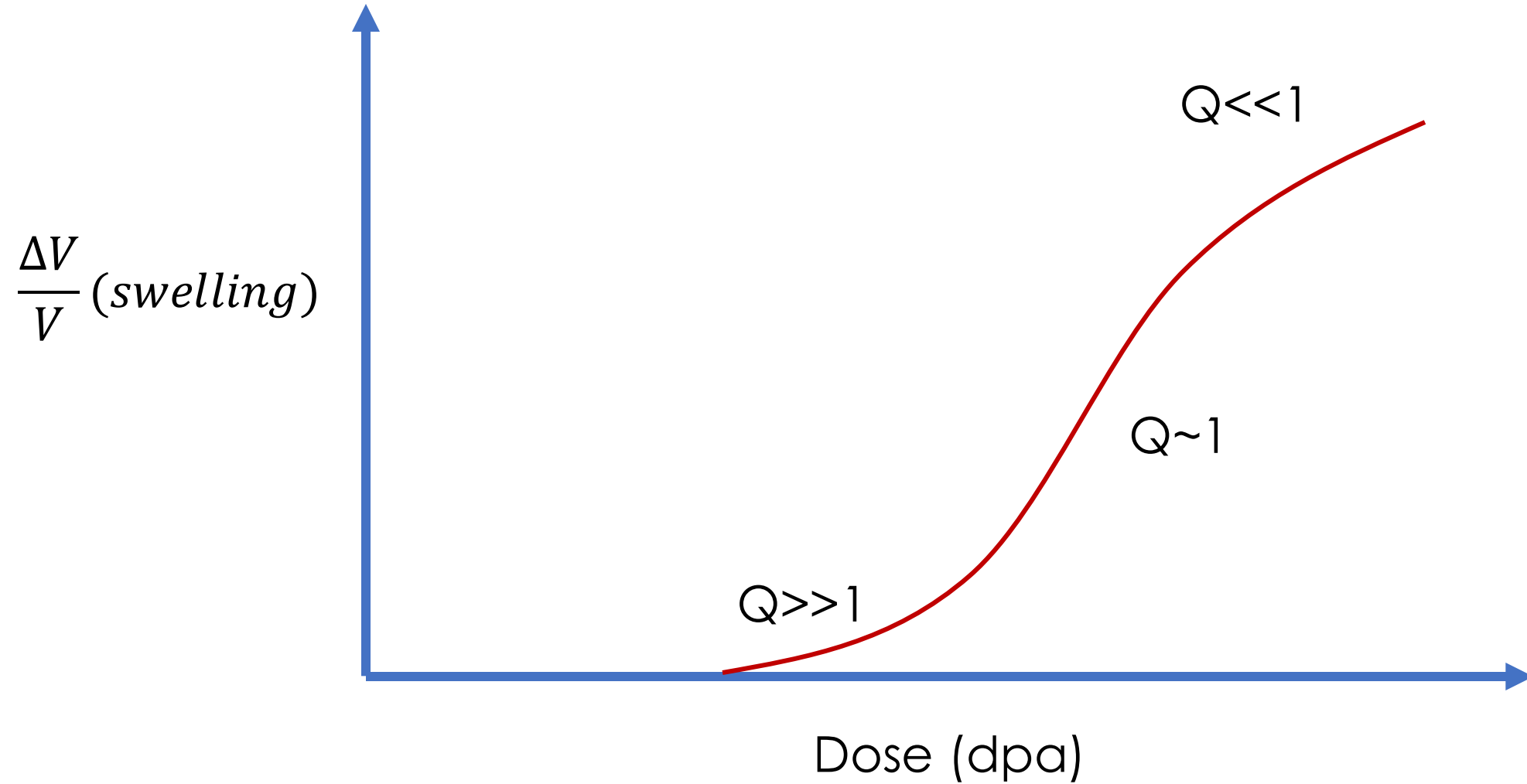
$$R\dot{R}_{th} = -\frac{D_v C_v^0 \Omega^2 z_v \rho_d}{kT(4\pi RN + z_v \rho_d)} (e^y - 1)$$

Effect of Structure on Void Swelling

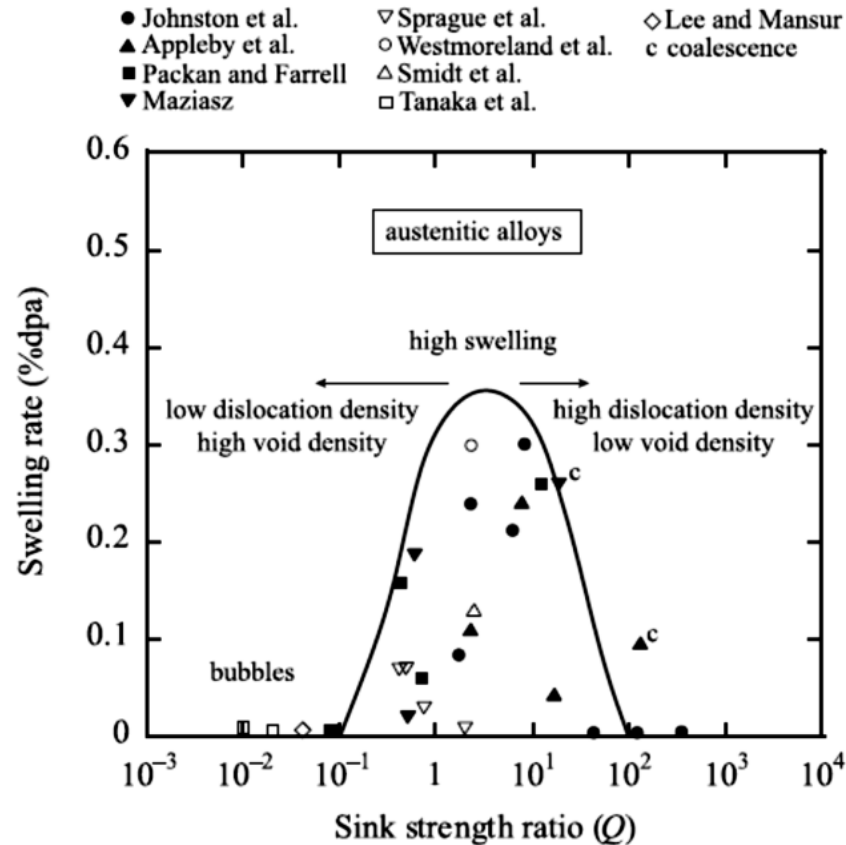
- Ferritic steels swell at rates $\sim 0.2\%/dpa$
- Structure alone is not sufficient to explain the difference between α -Fe (BCC) and γ -Fe (FCC)
- BCC vanadium alloys can swell at rates more like austenitic steels
- Difference is likely in the relative bias for point defects at sinks
- If the bias is removed: $z_i = z_v$, void growth is impossible
- Recall the 3rd term, put simply:

$$\left. \frac{z_v \rho_d}{(4\pi R \rho_v + z_v \rho_d)(4\pi R \rho_v + z_i \rho_d)} \right\} \frac{Q}{(1 + Q)^2} \quad \text{Where:} \quad Q = \frac{\rho_d z_i}{z_v 4\pi R \rho_v}$$

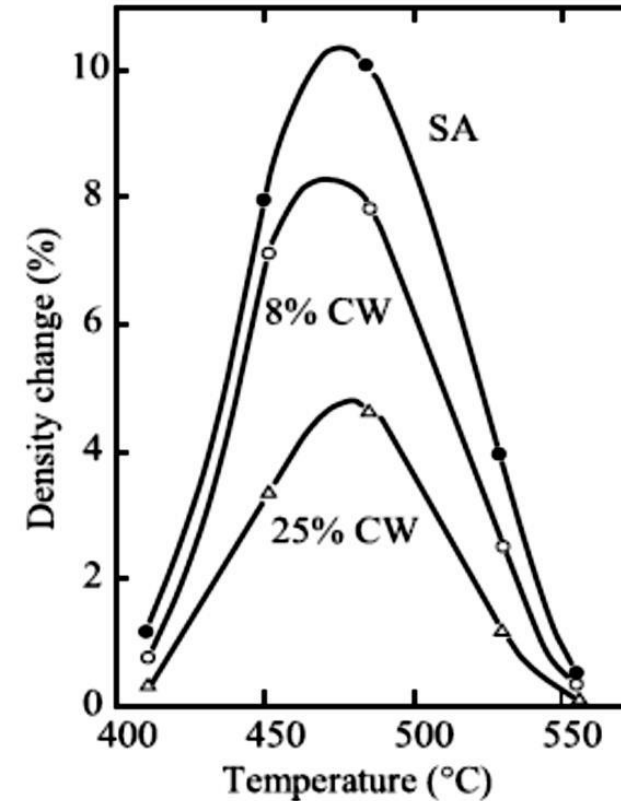
The Q-factor for structure dependence on dose



Effect of Structure on Void Swelling



*Experimentally observed swelling rates as a function of Q for austenitic stainless steels (Mansur LK (1994) *J NuclMater* 216:97–123)*



Dependence of swelling on cold-work for various temperatures for 316 stainless steel irradiated in the RAPSODIE reactor to doses of 20–71 dpa (Dupouy JM, Lehmann J, Boutard JL (1978) In: Proceedings of the Conference on Reactor Materials Science, vol. 5, Alushta, USSR. Moscow, USSR Government, pp 280–296)

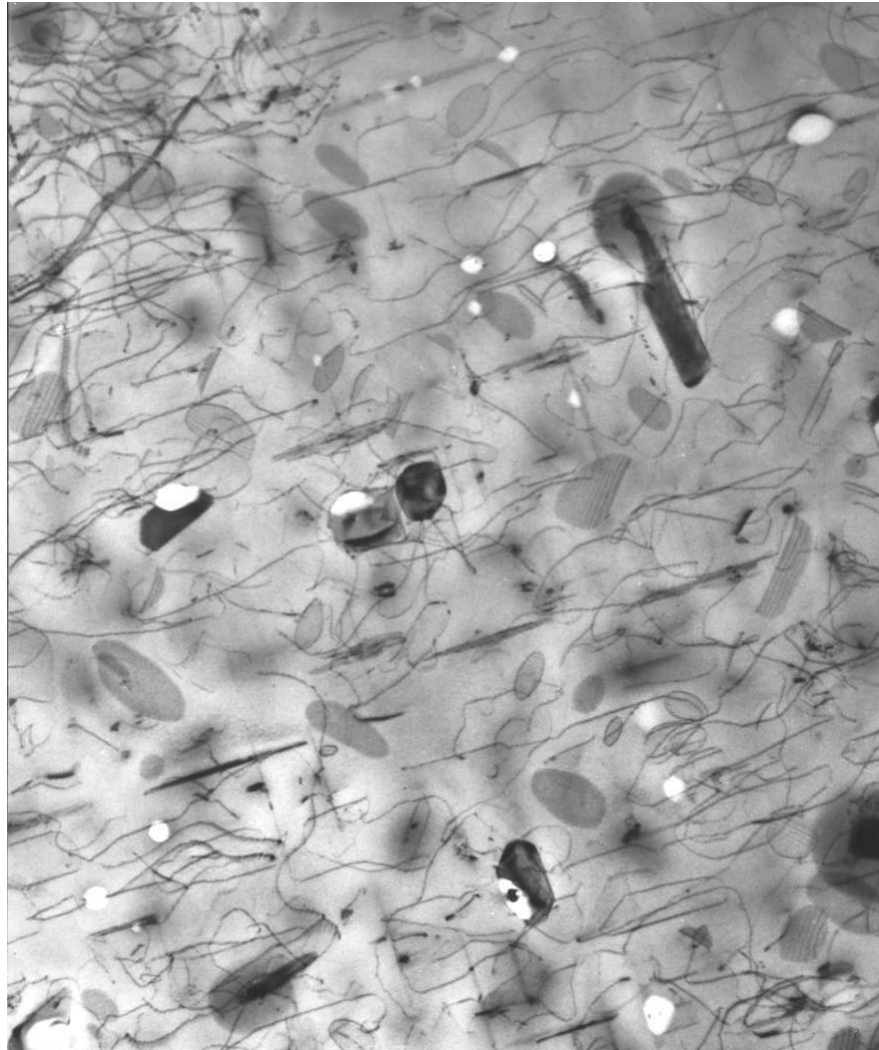
- Growth rate is maximum when $Q \sim 1$
- Growth decreases for $Q \neq 1$
- Observed experimentally
- CW reduces swelling because $Q \gg 1$

Based in Zeeland, Michigan, the iconic furniture company Herman Miller revolutionized office design forever when employee Robert Propst invented a modular, customizable system designed to give employees privacy and space. What year did Herman Miller introduce this invention, now famously known as the cubicle?

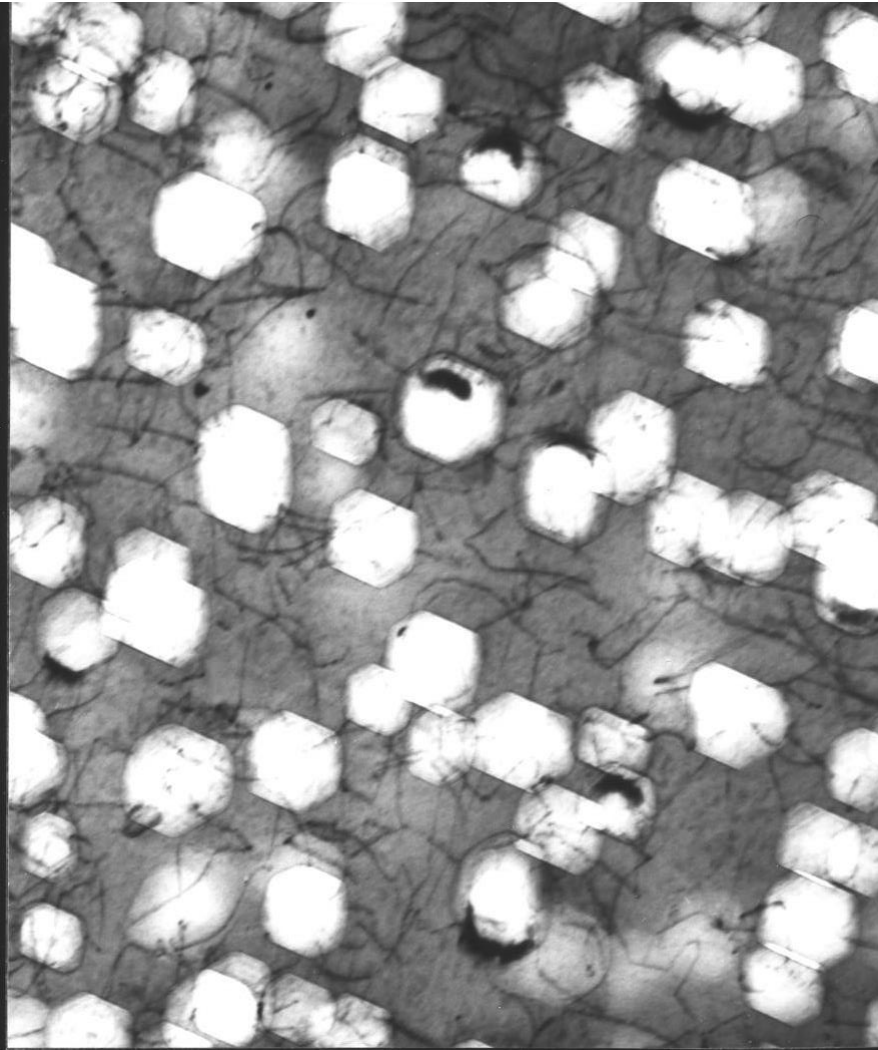


Image of voids + effect of sink strength

Commercial 316 SS (high sink strength)

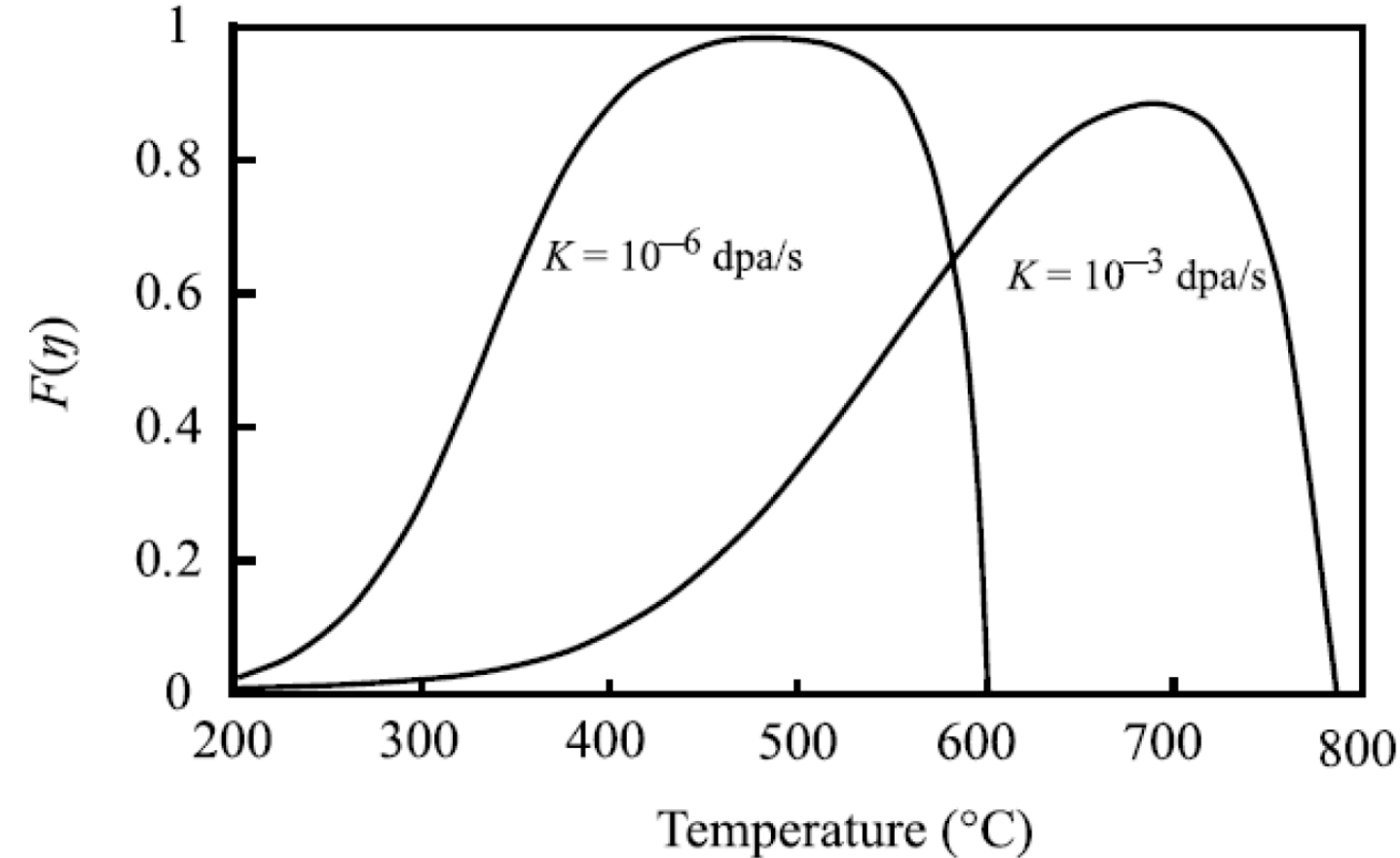


High-purity (low sink strength)



100 nm

Effect of Dose Rate



Dose rate is captured in the **fourth term** where:

$$F(\eta) = 2(\sqrt{1 + \eta} - 1) / \eta$$

And:

$$\eta = \frac{4K_0K_{iv}}{D_iD_v(4\pi R\rho_v + z_vp_d)^2}$$

Effect of Dose Rate

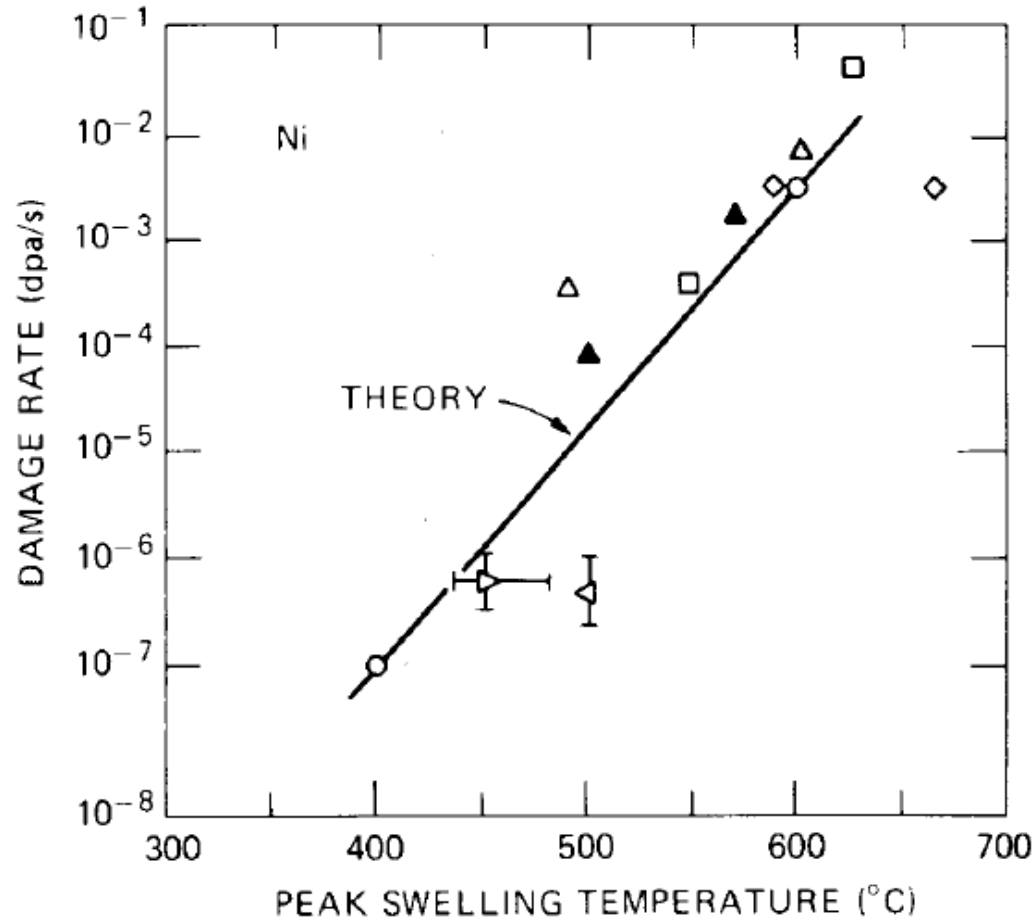


Figure 8.29. Compilation of experimental results for peak swelling temperature as a function of dose rate. Theoretically predicted trend is shown as the line. After Refs. 140 and 141.

Dose rate is captured in the **fourth term** where:

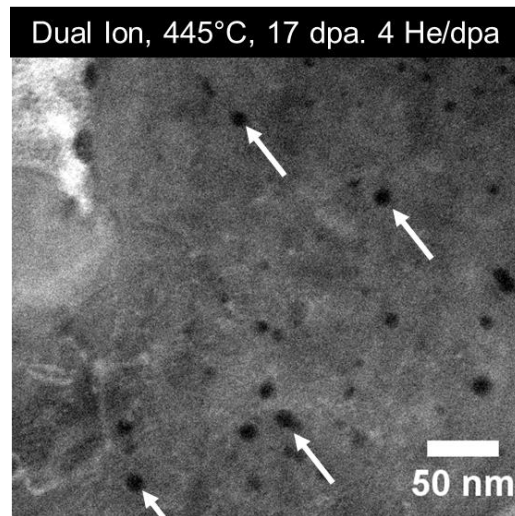
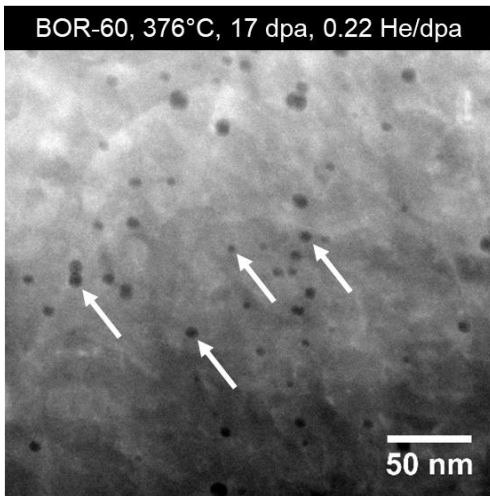
$$F(\eta) = 2(\sqrt{1 + \eta} - 1) / \eta$$

And:

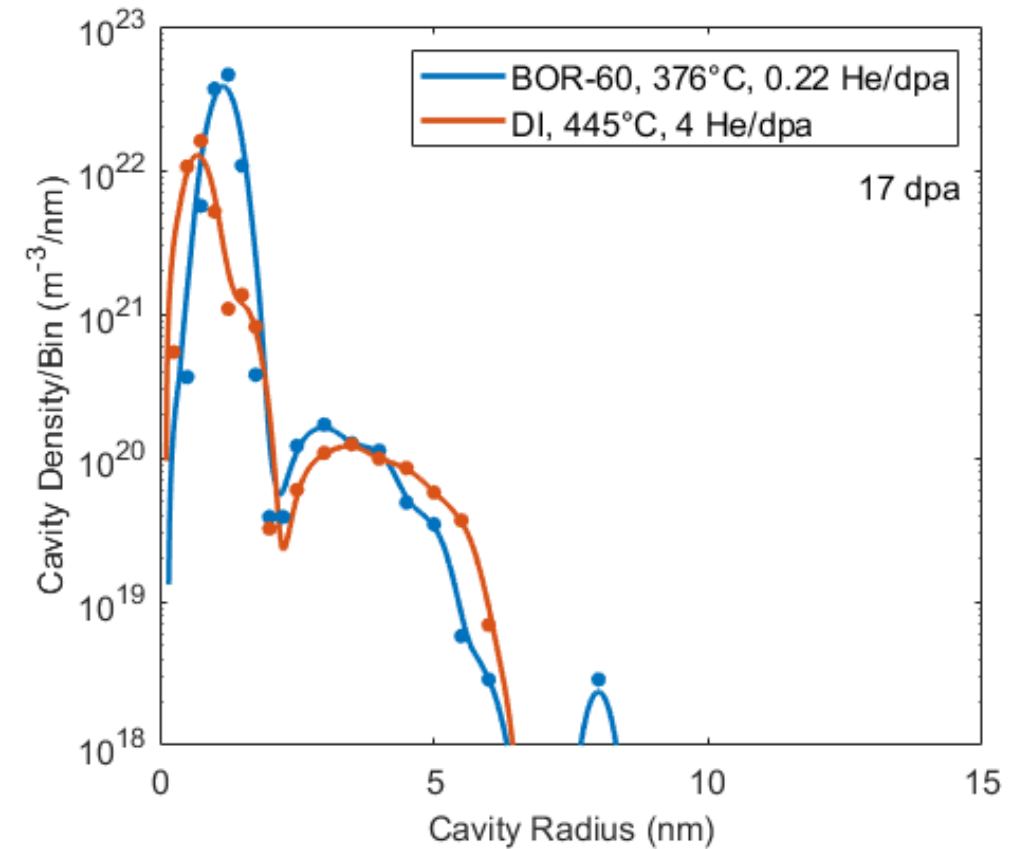
$$\eta = \frac{4K_0K_{iv}}{D_iD_v(4\pi R\rho_v + z_vp_d)^2}$$

Effect of Dose Rate – Real World Example

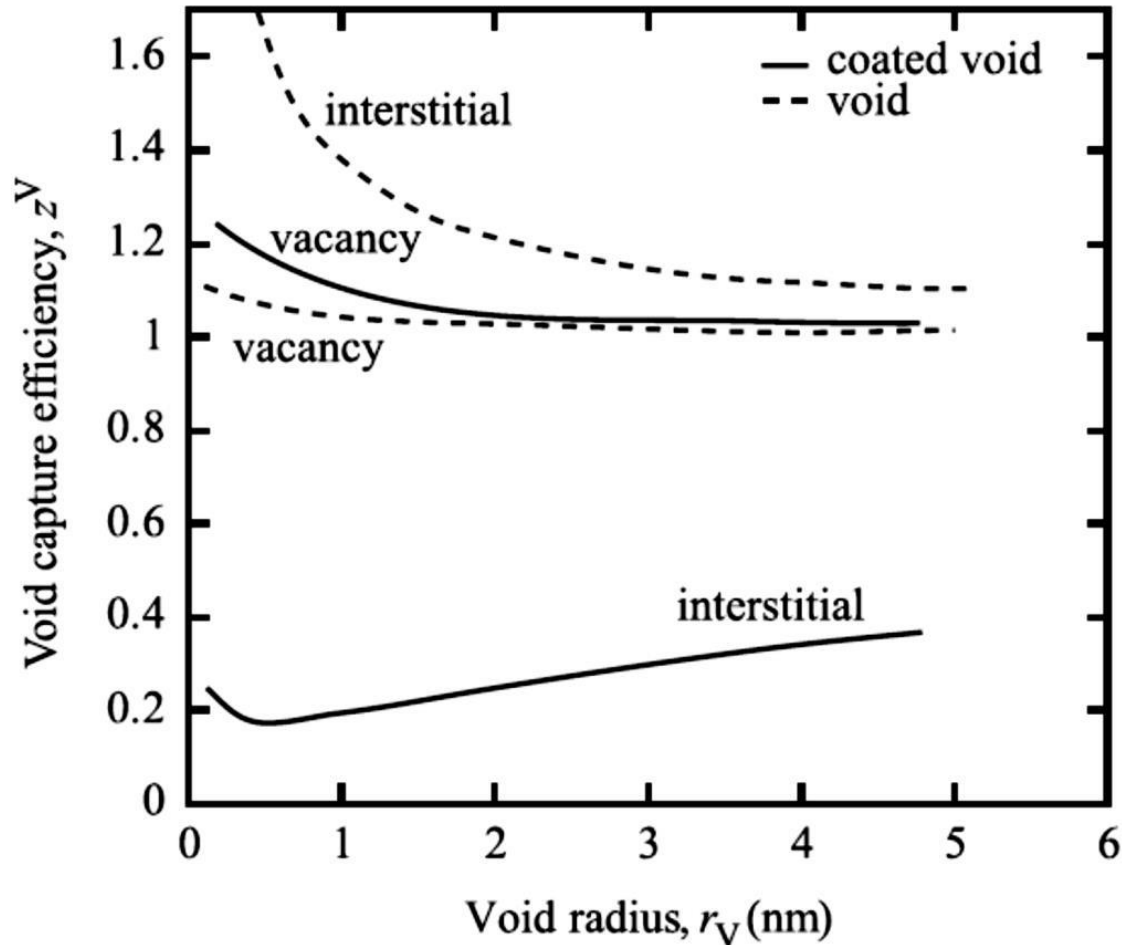
STEM HAADF



$$T_2 - T_1 = \frac{\frac{kT_1^2}{E_v^m + 2E_v^f} \ln\left(\frac{G_2}{G_1}\right)}{1 - \frac{kT_1}{E_v^m + 2E_v^f} \ln\left(\frac{G_2}{G_1}\right)}$$



Effect of void surface segregation on defect bias



- For a bare unpressurized void, interstitial bias is greater than vacancy bias. Voids will shrink
- If “shell” shear modulus or lattice parameter is greater than matrix shear modulus, vacancy bias becomes greater than interstitial bias
 - This effect can occur because of radiation induced segregation
- Thicker shells have a greater effect

Capture efficiency for point defects diffusion to a void and a coated void as a function of void radius RV . (W.G. Wolfer, L.K. Mansur, The capture efficiency of coated voids, *Journal of Nuclear Materials*, Volume 91, Issue 2, 1980, Pages 265-276)

Effect of Inert Gas: Bubbles & Voids

- Inert gas atoms (H, He, etc.) are created by transmutation and interact with vacancies
 - Must be accounted for on bubble/void growth as:
 - Insoluble gas atoms can act as immobile nucleation sites to which vacancies and interstitials migrate to form voids
 - Inert gas atoms can stabilize a cavity and assist the nuclei during nucleation and growth
- First, let's assume the following:
 - No account taken of cascades or lattice imperfections
 - Gas atom association is stable and mobile

Side Note!

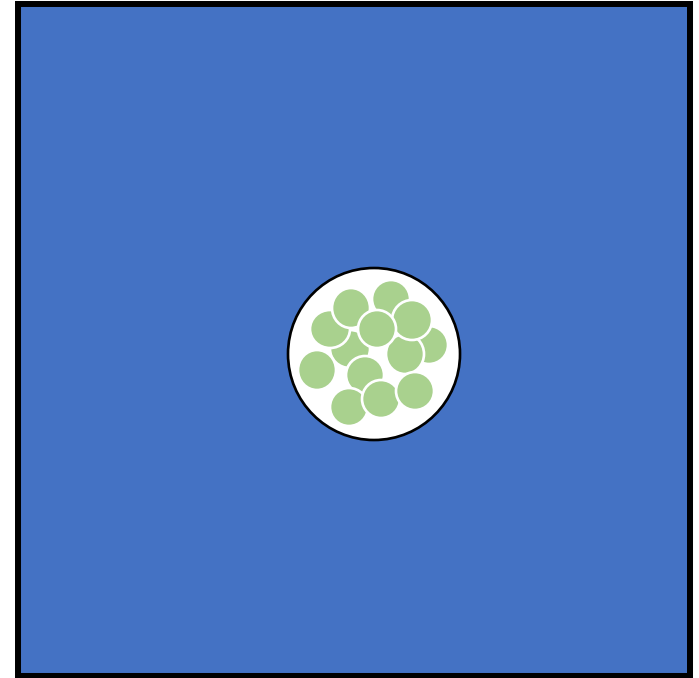
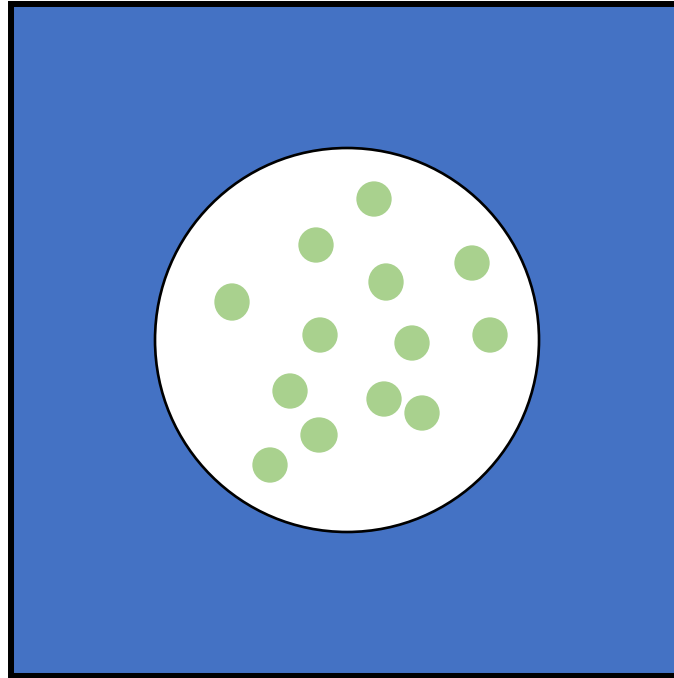
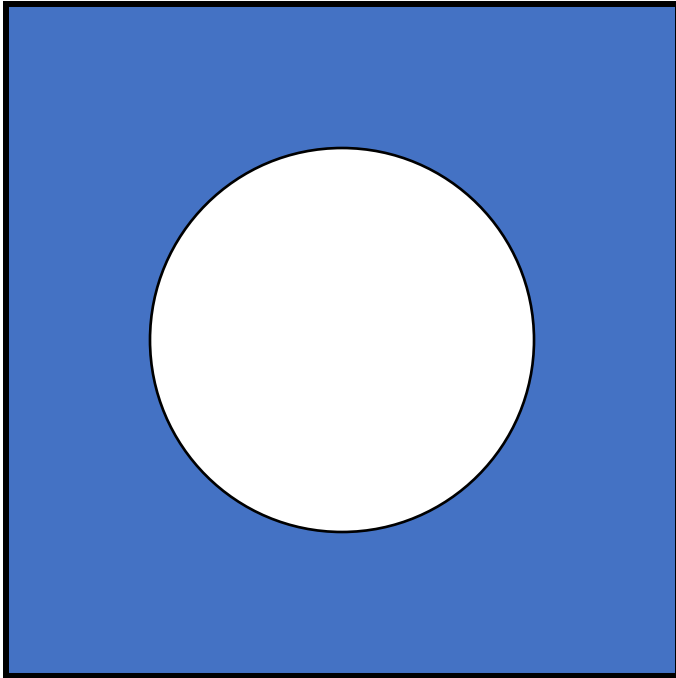
We generally define the following:

Void: open volume in a solid not pressurized by inert gas

Bubble: open volume in a solid that is pressurized by inert gas

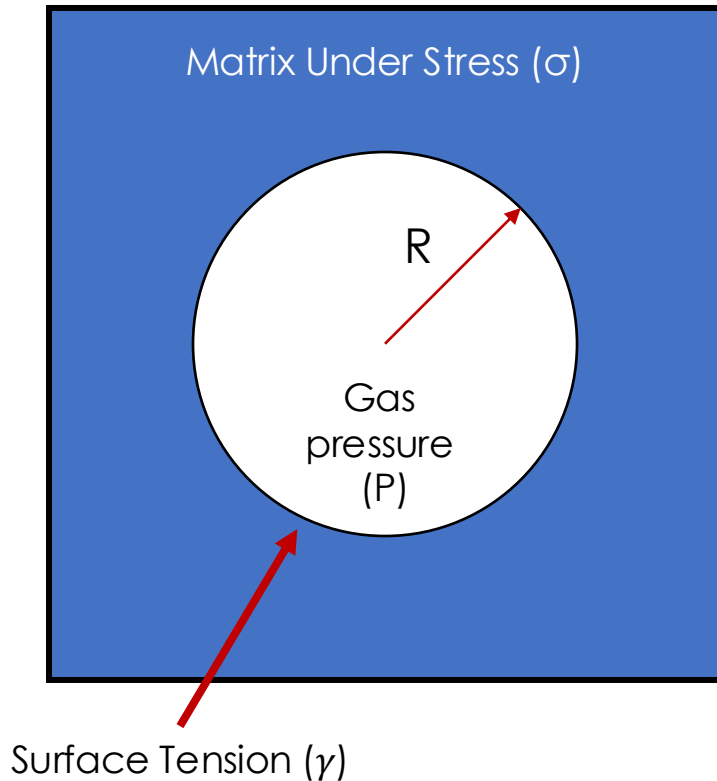
Cavity: Generalization for open volume in a solid – can be a bubble or void

Effect of Inert Gas: Bubbles & Voids



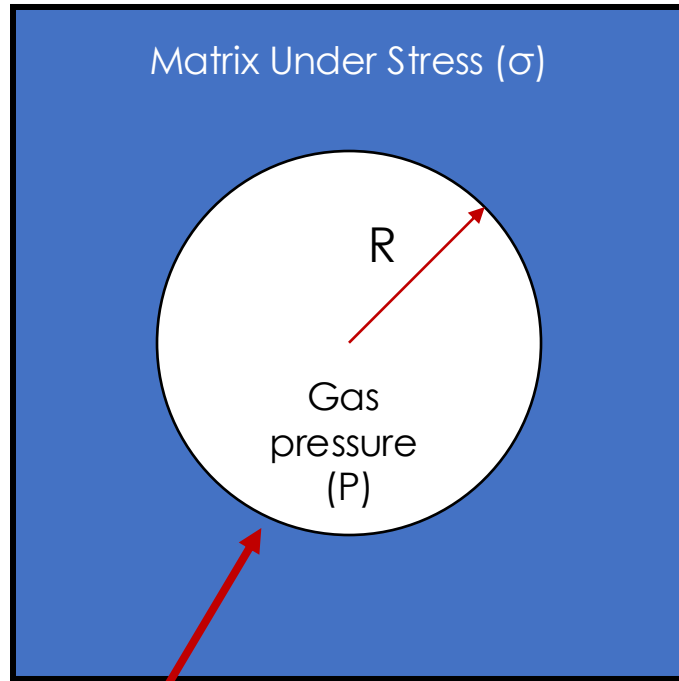
Effect of Inert Gas: Bubbles & Voids

- For a spherical cavity, the change in volume and surface area is:
- Under expansion (cavity growth) the pressure does work on $P dV$ and the surface energy increase by γdA , or simply,
- If not at mechanical equilibrium, then:



Effect of Inert Gas: Bubbles & Voids

- Let's now calculate the number of gas atoms present in the bubble, using the ideal gas law:



- Remembering that $P = \frac{2\gamma}{r}$ and plugging in we get:

Effect of Inert Gas: Bubbles & Voids

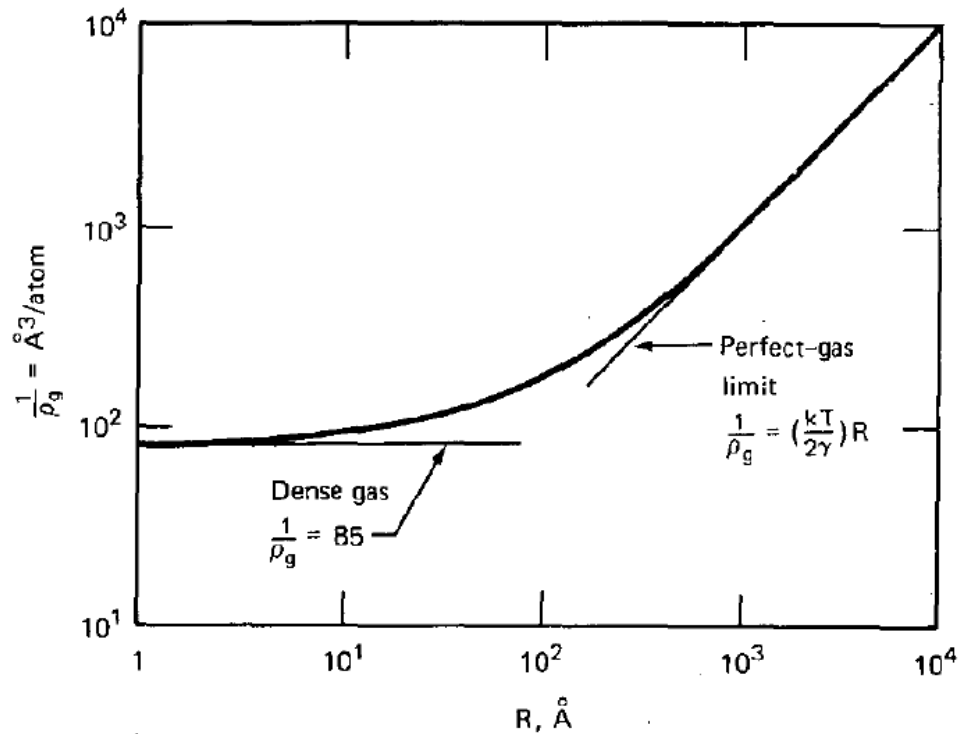


Fig. 13.3 Density of xenon gas in a spherical bubble imbedded in a stress-free solid of surface tension of 1000 dynes/cm.

For most applications we assume an ideal gas in mechanical equilibrium

- To account for non-ideal gas (e.g. high pressure in small bubbles) we need a different eq'n of state:
- We can then solve for n_x again using this relationship to get the number of gas atoms in the **dense gas limit**:

$$n_x = \frac{\frac{4}{3}\pi r^3}{B + \left(k_b T / 2\gamma\right)r}$$

And for non-equilibrium bubbles:

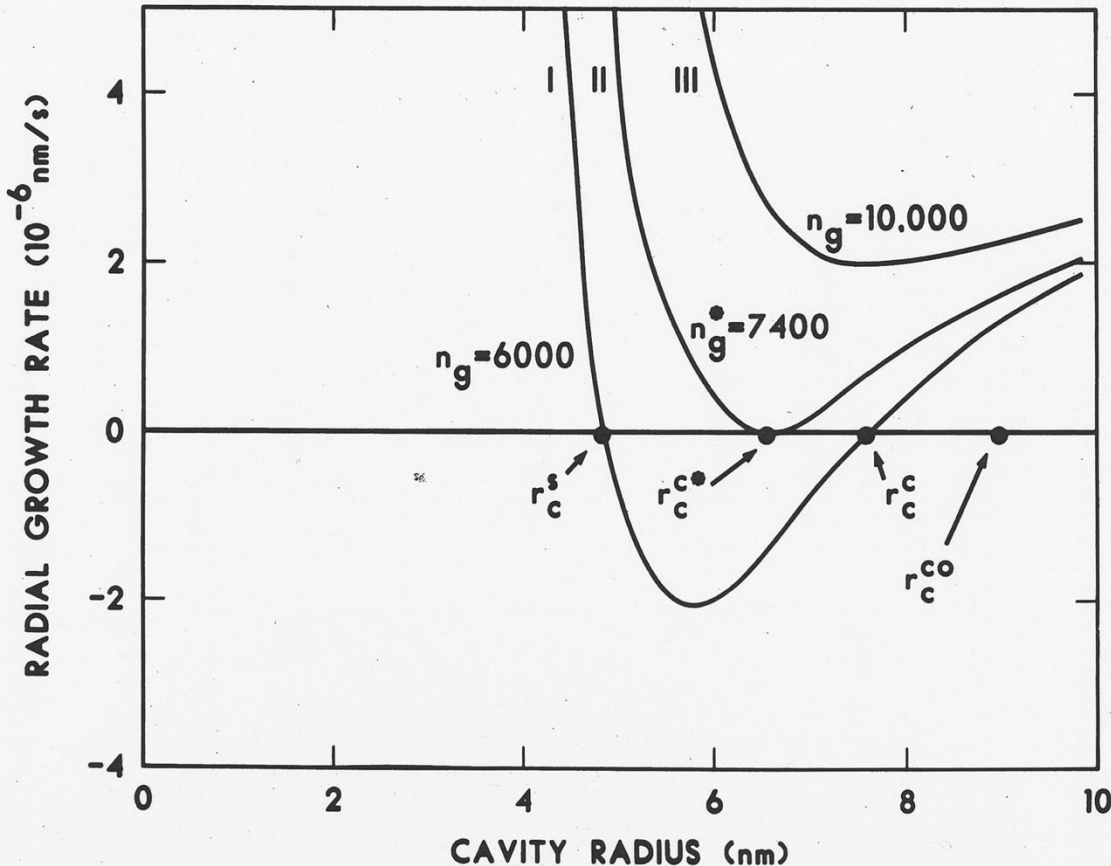
$$n_x = \frac{128\pi\gamma^3}{81\sigma_c^2 k_b T}$$

Now that we have an expression for n_x and P , we can add these into the terms for the growth rate law including thermal emission, we then get:

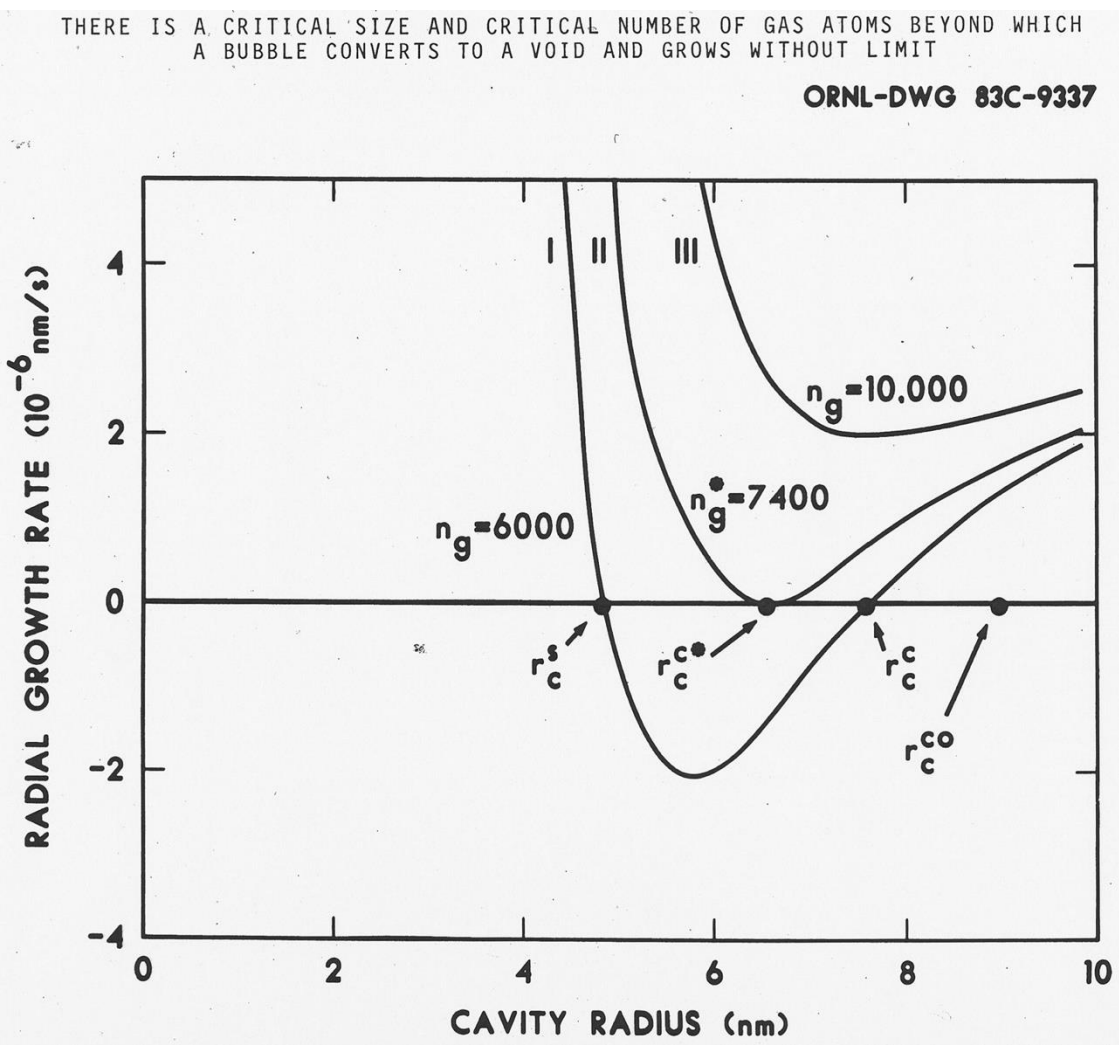
$$R\dot{R} = K_o\Omega \left(\frac{z_i - z_v}{z_v} \right) \frac{z_v\rho_d}{(4\pi R\rho_v + z_v\rho_d)^2} F(\eta) - \frac{D_v C_v^0 \Omega^2 z_v \rho_d}{kT(4\pi R N + z_v \rho_d)} \left(\frac{2\gamma}{R} - \frac{n_x kT}{4/3 \pi R^3 - n_x B} \right)$$

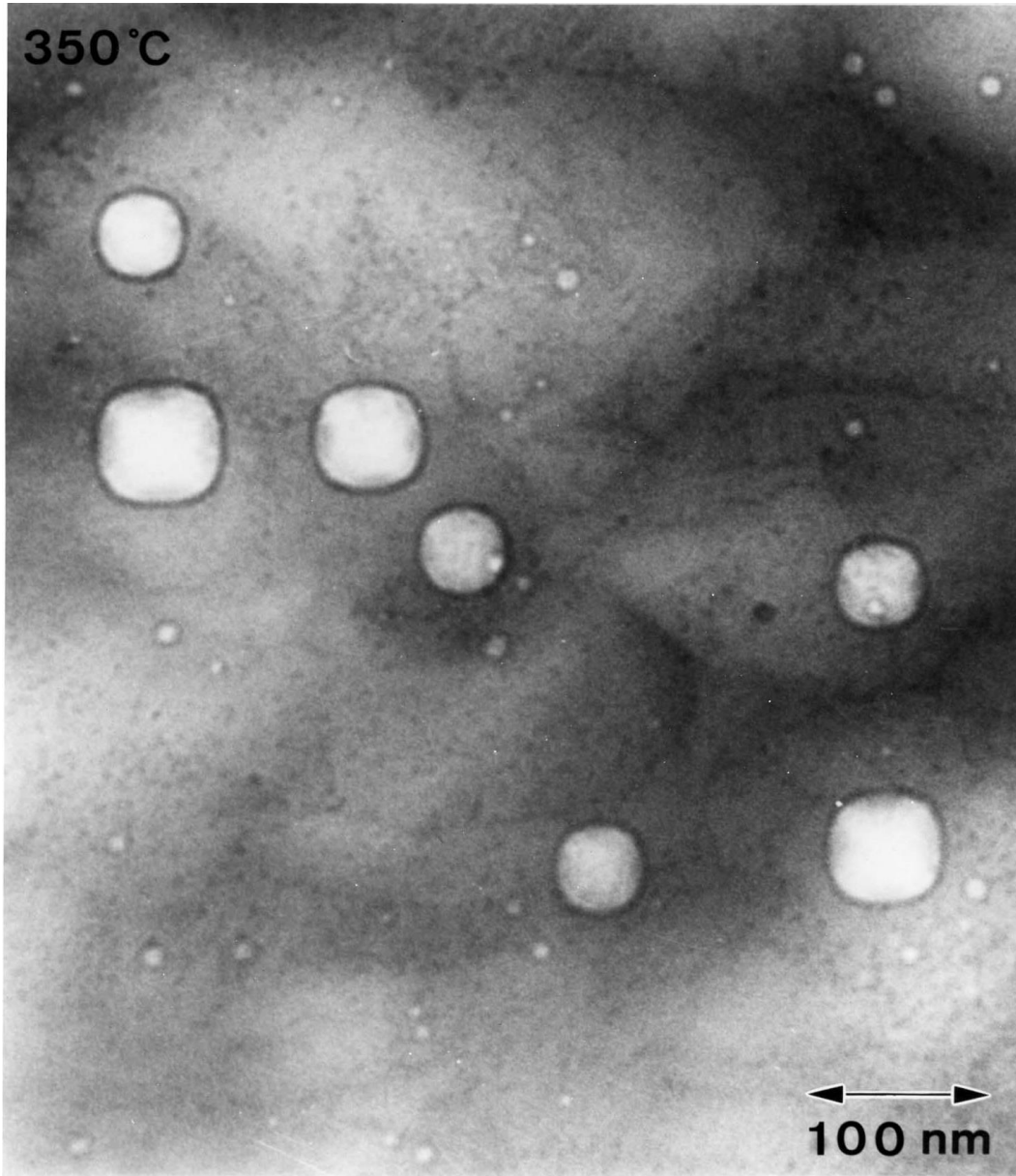
THERE IS A CRITICAL SIZE AND CRITICAL NUMBER OF GAS ATOMS BEYOND WHICH A BUBBLE CONVERTS TO A VOID AND GROWS WITHOUT LIMIT

ORNL-DWG 83C-9337



When gas is present, the current models predicts that cavities containing less than n_g^* gas atoms remain at or below r_c^* , but those with more than n_g^* , this creates a bimodal distribution

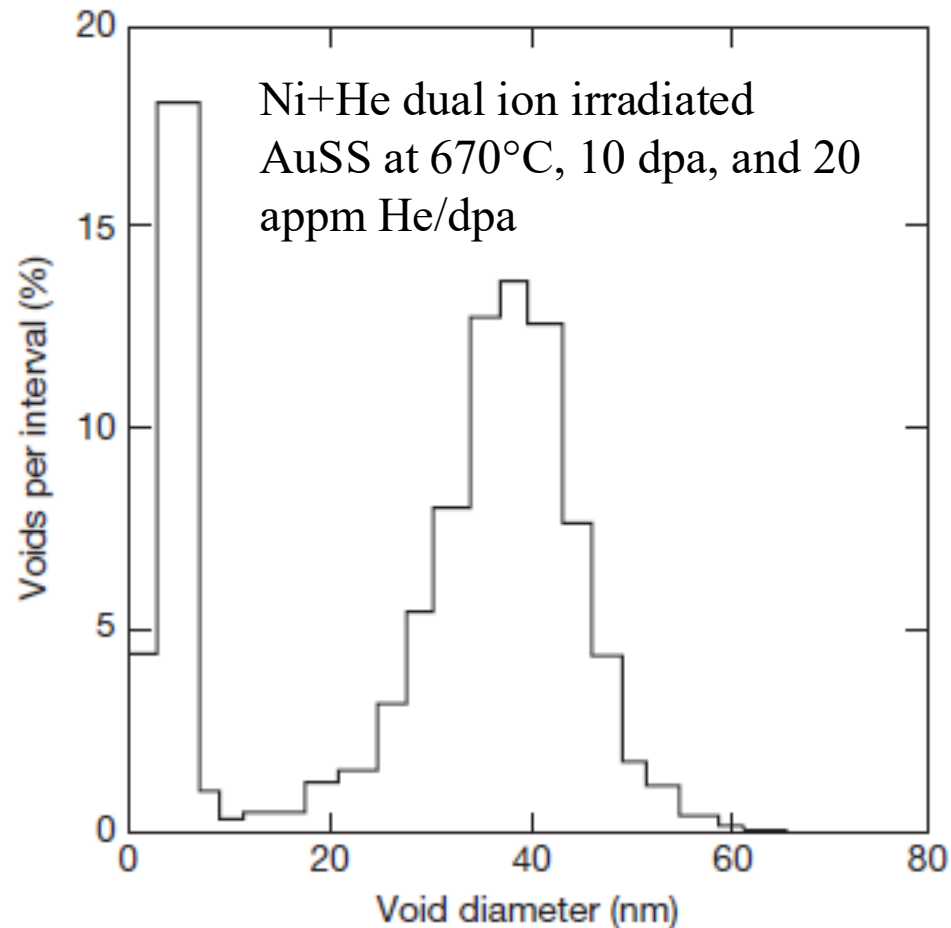




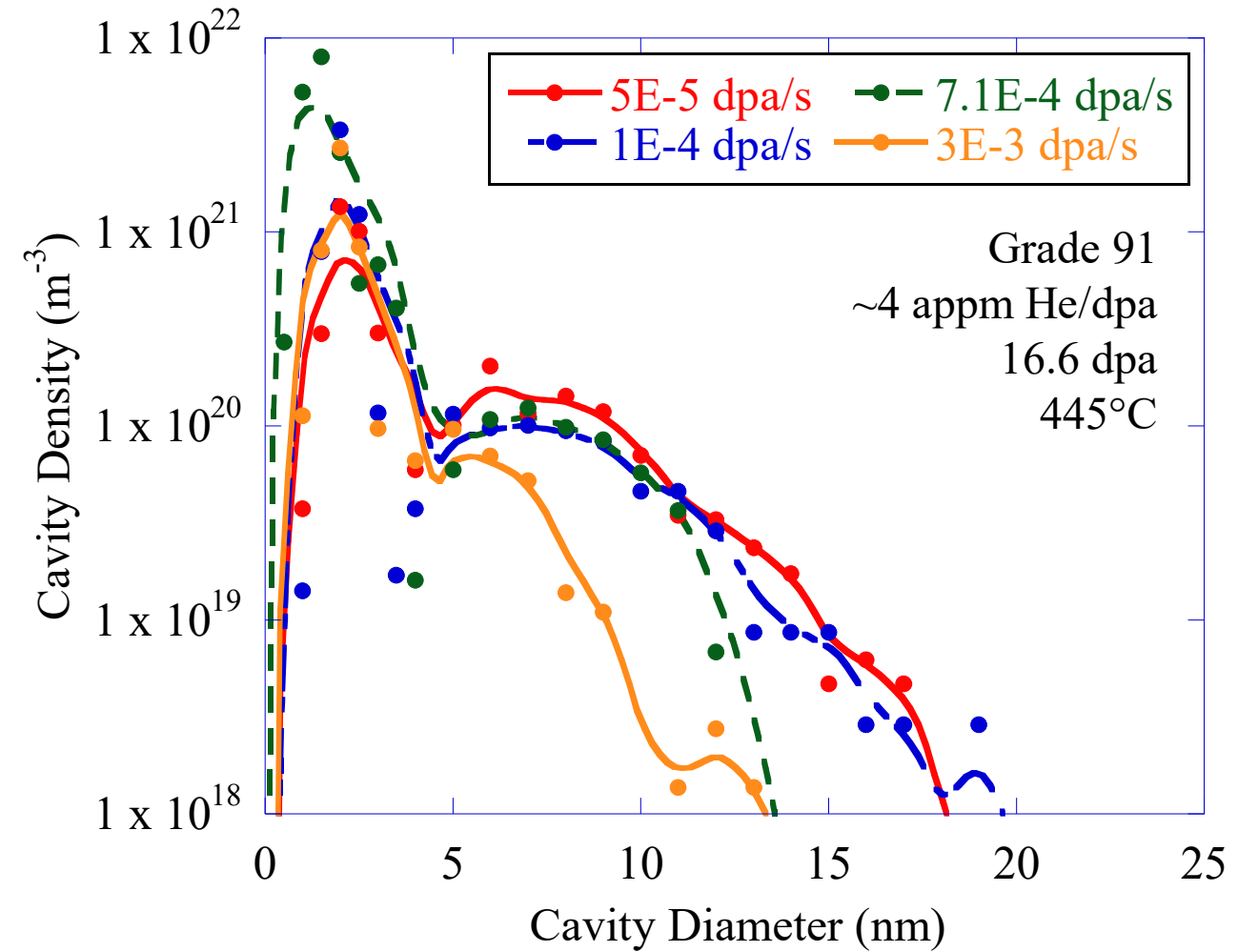
Void and He
bubble formation in
Cu-100 ppm B
following fission
neutron irradiation
to 1.2 dpa at 350°C

Zinkle, Farrell and Kanazawa, J. Nucl. Mater. 179-191 (1991) 994

Experimental examples

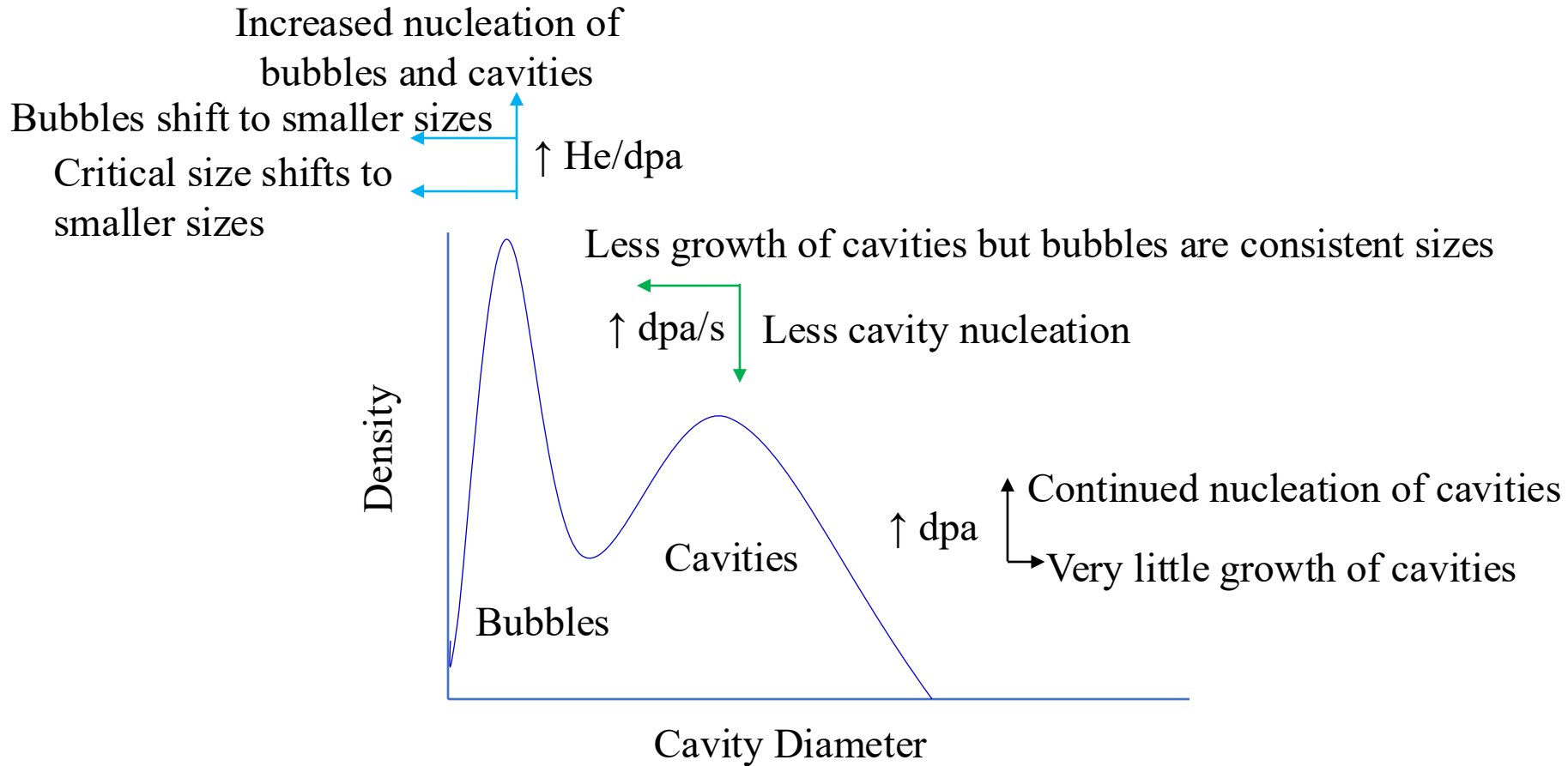


Mansur, Coghlan JNM 119 (1983)



Taller (2019)

Experimental examples

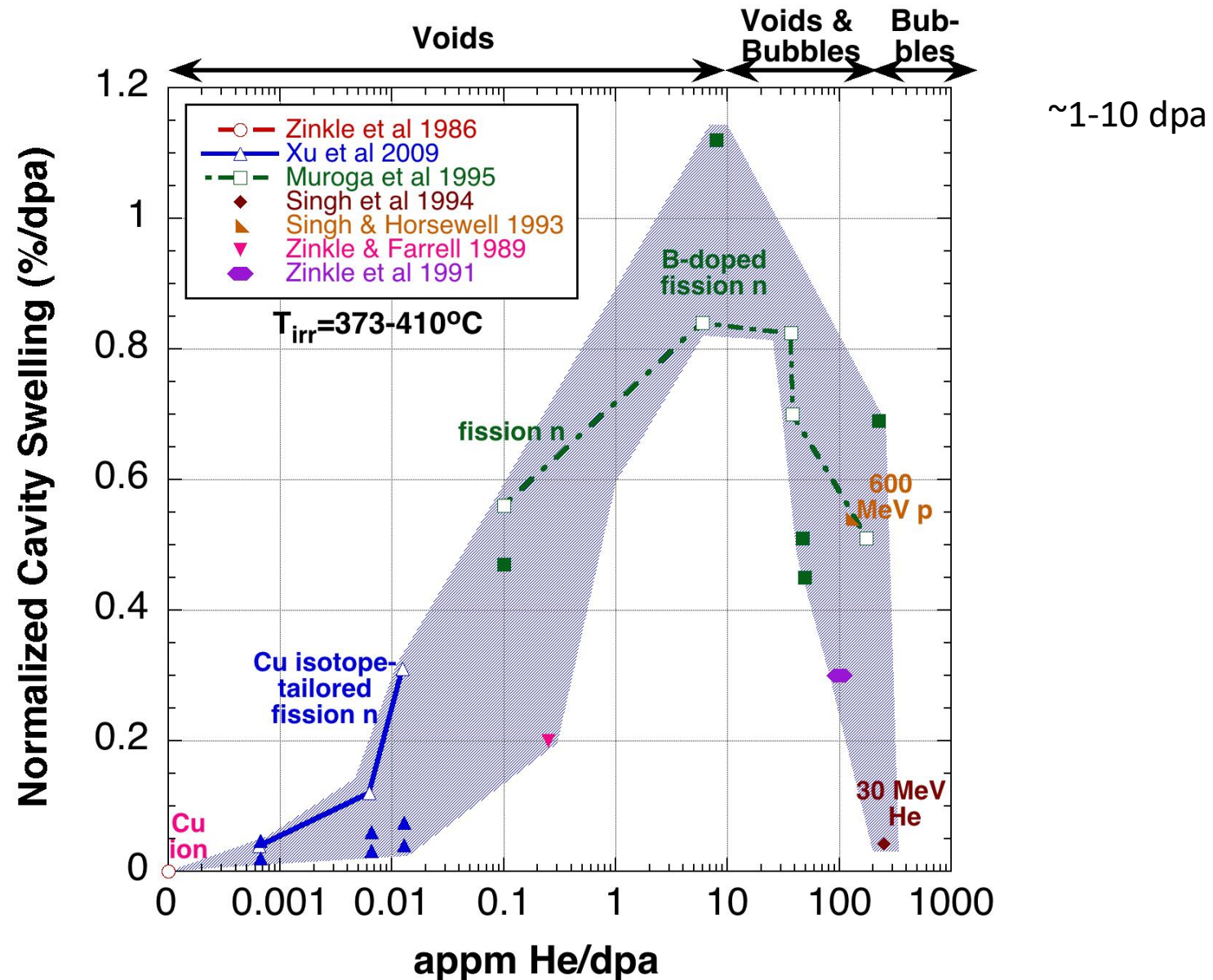


Fixed dpa/s – Variable He/dpa

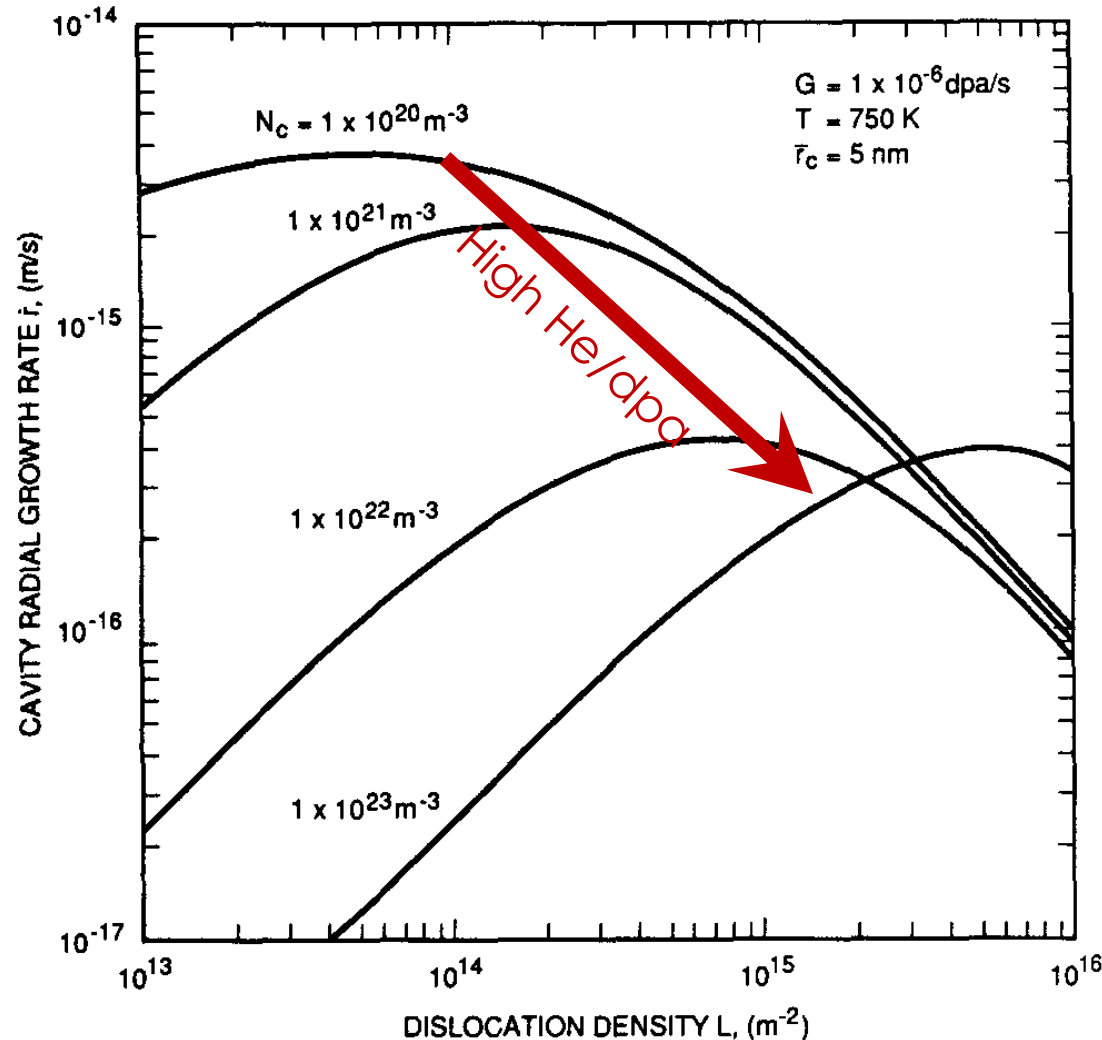
Fixed He/dpa – Variable dpa/s

Increase in dpa for constant He/dpa and dpa/s

Cavity swelling vs. He/dpa ratio in irradiated copper

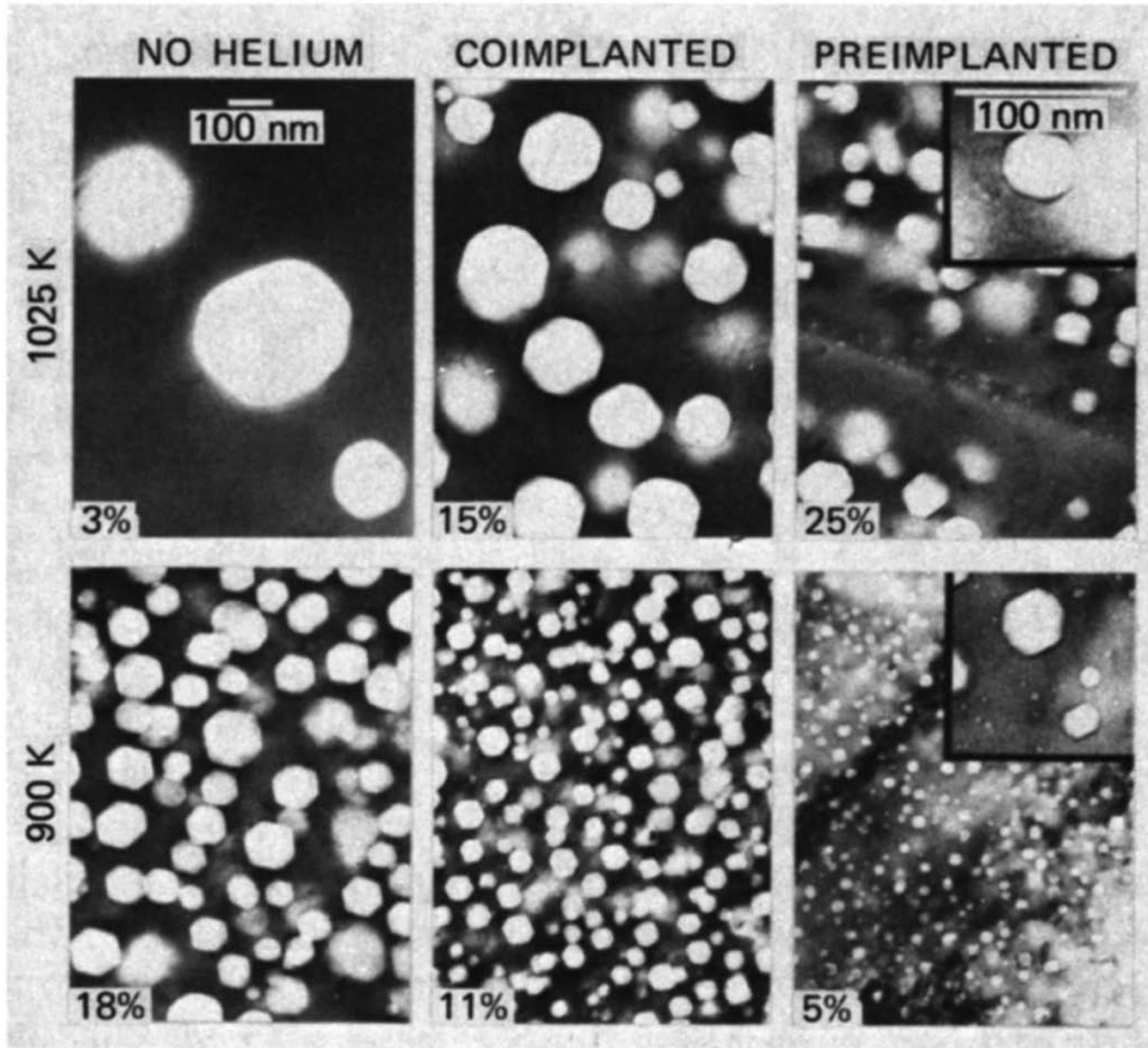


Calculated void growth rate is typically reduced for high cavity and dislocation sink strengths



Over nucleation of cavities due to too high He/dpa can suppress void swelling

Effect of He in ion irradiations



Implantation method of He can drastically effect swelling in ion irradiated materials

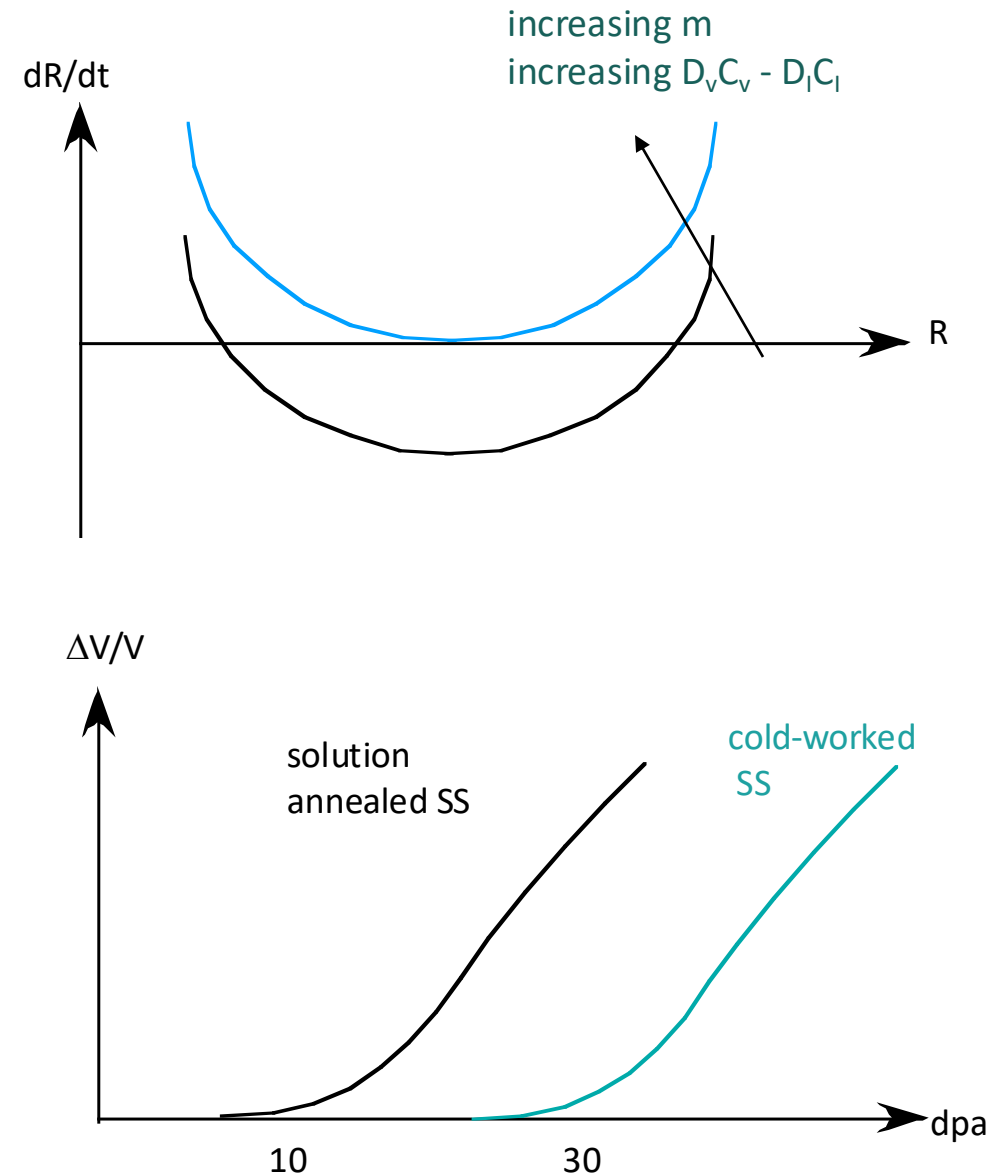
Image of Fe-17Cr-16.7Ni-2.5Mo

Packan & Farrell, NT-Fusion, 1983

Remedies for void swelling?

Remedies for void swelling?

- Decrease $D_v C_v - D_l C_l$ arriving at cavity;
- Eliminate He gas production (expensive or impractical)
- Reduce C_v, C_l :
 - increase recombination
 - add precipitates or dispersoids (TiC/TiO₂) to act as recombination sink, trap He and stabilize dislocations
 - increase other sink strengths
 - add dislocations (cold-work); generally only effective for low to moderate doses
 - introduce nanoscale grain boundaries



Questions?

